



惠州MPS6520供应商

捷多邦 专业PCB打样工厂 24小时加急出货

COMPLEMENTARY
SILICON TRANSISTORS

MPS6520, MPS6521 (NPN) and MPS6522, MPS6523 (PNP) are complementary silicon planar epitaxial transistors designed for general purpose amplifier applications and for complementary circuitry.

ABSOLUTE MAXIMUM RATINGS

		MPS6520, 1	MPS6522, 3
Collector-Base Voltage	V_{CB0}	40V	25V
Collector-Emitter Voltage	V_{CE0}		25V
Emitter-Base Voltage	V_{EB0}		4V
Collector Current	I_C		100mA
Total Power Dissipation @ $T_A=25^\circ\text{C}$ $T_C=25^\circ\text{C}$	P_{tot}		350mW 1W
Operating Junction & Storage Temperature	T_j, T_{stg}	-55 to +150°C	

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV_{CE0}	25		V	$I_C=0.5\text{mA}$ $I_B=0$
Emitter-Base Breakdown Voltage	BV_{EB0}	4		V	$I_E=10\mu\text{A}$ $I_C=0$
Collector Cutoff Current	I_{CB0}				
	MPS6520, 1		50	nA	$V_{CB}=30\text{V}$ $I_E=0$
	MPS6520, 1		1	μA	$V_{CB}=30\text{V}$ $T_A=60^\circ\text{C}$
	MPS6522, 3		50	nA	$V_{CB}=20\text{V}$ $I_E=0$
	MPS6522, 3		1	μA	$V_{CB}=20\text{V}$ $T_A=60^\circ\text{C}$
D.C. Current Gain	H_{FE}	100			$I_C=100\mu\text{A}$ $V_{CE}=10\text{V}$
	MPS6521, 3	150			
	MPS6520, 2	200			$I_C=2\text{mA}$ $V_{CE}=10\text{V}$
	MPS6521, 3	300			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.5	V	$I_C=50\text{mA}$ $I_B=5\text{mA}$

MICRO ELECTRONICS LTD. 美科有限公司

38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro HX.

P.O. Box 49477, Kwun Tong. Tel: 3-430181-6 3-802362, 3-802423, 3-898224

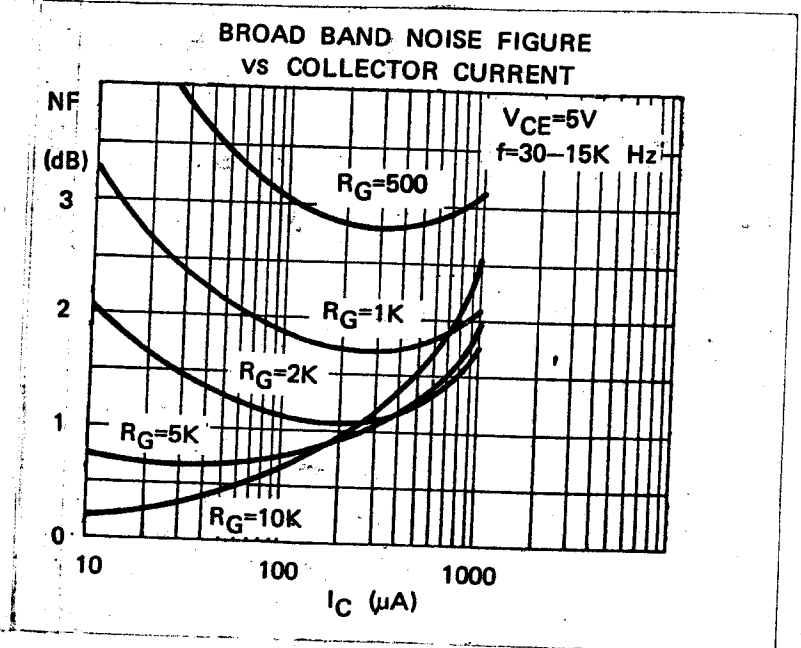
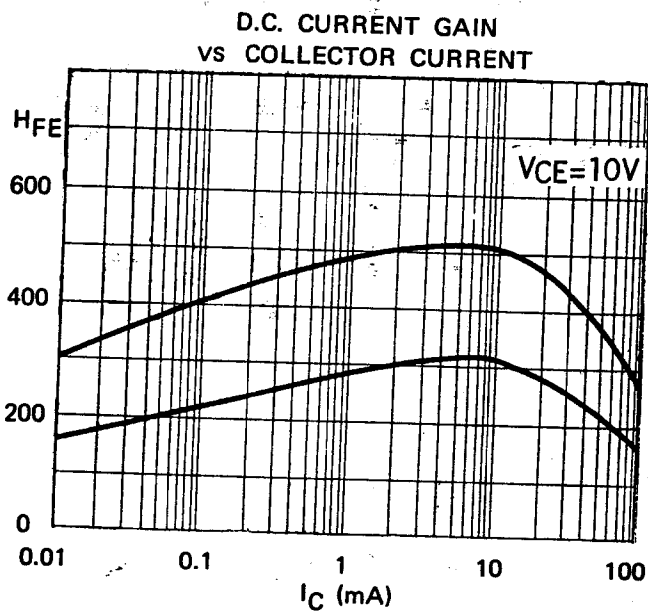
FAX: 3-410321



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

PARAMETER	SYMBOL	TYP	MAX	UNIT	TEST CONDITIONS	
Current Gain-Bandwidth Product	f_T			MHz	$I_C=2\text{mA}$ $V_{CE}=10\text{V}$	
		MPS6520, 1	390			
		MPS6522, 3	340			
		MPS6520, 1	480		$I_C=10\text{mA}$ $V_{CE}=10\text{V}$	
		MPS6522, 3	420			
Output Capacitance	C_{ob}		3.5	pF	$V_{CB}=10\text{V}$ $I_E=0$ $f=1\text{MHz}$	
Noise Figure	NF	1.8	3	dB	$I_C=10\mu\text{A}$ $V_{CE}=5\text{V}$ $R_S=10\text{k}\Omega$ $f=10\text{Hz}$ to 10kHz $BB=15.7\text{kHz}$	

TYPICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)



out 29.00